

# TSM240N03CX6

## 30V N-Channel Power MOSFET



**Pin Definition:**

1. Drain	6. Drain
2. Drain	5. Drain
3. Gate	4. Source

### Key Parameter Performance

Parameter	Value	Unit
$V_{DS}$	30	V
$R_{DS(on)}$ (max)	$V_{GS} = 10V$	24
	$V_{GS} = 4.5V$	34
$Q_g$	4.1	nC

### Features

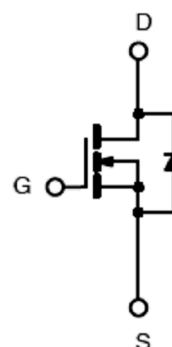
- Halogen-free
- Improved  $dV/dt$  capability
- Fast Switching

### Ordering Information

Part No.	Package	Packing
TSM240N03CX6 RFG	SOT-26	3kpcs / 7+Reel

**Note:** %G+denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

### Block Diagram



N-Channel MOSFET

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	$T_C = 25^\circ C$	6.5
		$T_C = 100^\circ C$	4.1
Pulsed Drain Current <sup>(Note 1)</sup>	$I_{DM}$	26	A
Single Pulse Avalanche Energy <sup>(Note 2)</sup>	$E_{AS}$	32	mJ
Power Dissipation @ $T_C = 25^\circ C$	$P_D$	1.56	W
Operating Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature Range	$T_{STG}$	-55 to +150	$^\circ C$

### Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Ambient	$R_{JA}$	80	$^\circ C/W$

### Electrical Specifications ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

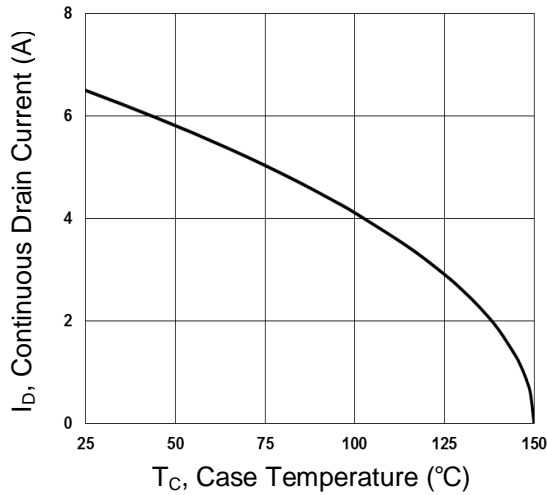
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu\text{A}$	$BV_{DSS}$	30	--	--	V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 6A$	$R_{DS(on)}$	--	17	24	m
	$V_{GS} = 4.5V, I_D = 4A$		--	22	34	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	$V_{GS(TH)}$	1.2	1.4	2.5	V
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	$I_{DSS}$	--	--	1	$\mu\text{A}$
	$V_{DS} = 24V, T_J = 125^\circ\text{C}$		--	--	10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	$I_{GSS}$	--	--	$\pm 100$	nA
Forward Transconductance <sup>(Note 3)</sup>	$V_{DS} = 10V, I_D = 4A$	$g_{fs}$	--	6.5	--	S
<b>Dynamic</b>						
Total Gate Charge <sup>(Note 3,4)</sup>	$V_{DS} = 15V, I_D = 6A,$ $V_{GS} = 4.5V$	$Q_g$	--	4.1	--	nC
Gate-Source Charge <sup>(Note 3,4)</sup>		$Q_{gs}$	--	1	--	
Gate-Drain Charge <sup>(Note 3,4)</sup>		$Q_{gd}$	--	2.1	--	
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0\text{MHz}$	$C_{iss}$	--	345	--	pF
Output Capacitance		$C_{oss}$	--	55	--	
Reverse Transfer Capacitance		$C_{rss}$	--	32	--	
<b>Switching</b>						
Turn-On Delay Time <sup>(Note 3,4)</sup>	$V_{DD} = 15V, I_D = 1A,$ $V_{GS} = 10V, R_{GEN} = 6$	$t_{d(on)}$	--	2.8	--	ns
Turn-On Rise Time <sup>(Note 3,4)</sup>		$t_r$	--	7.2	--	
Turn-Off Delay Time <sup>(Note 3,4)</sup>		$t_{d(off)}$	--	15.8	--	
Turn-Off Fall Time <sup>(Note 3,4)</sup>		$t_f$	--	4.6	--	
<b>Source-Drain Diode Ratings and Characteristic</b>						
Maximum Continuous Drain-Source Diode Forward Current	Integral reverse diode in the MOSFET	$I_S$	--	--	6.5	A
Maximum Pulse Drain-Source Diode Forward Current		$I_{SM}$	--	--	26	A
Diode-Source Forward Voltage	$V_{GS} = 0V, I_S = 1A$	$V_{SD}$	--	--	1	V

#### Note:

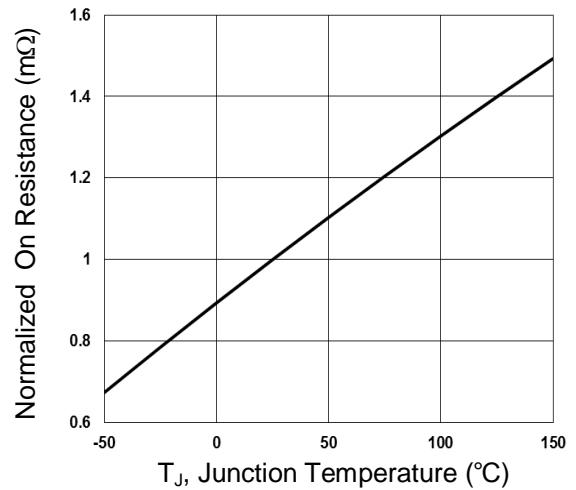
- Pulse width limited by safe operating area
- $L = 1\text{mH}, I_{AS} = 8A, V_{DD} = 25V, R_G = 25$  , Starting  $T_J = 25^\circ\text{C}$
- Pulse test: pulse width  $m300\mu\text{s}$ , duty cycle  $m2\%$
- Switching time is essentially independent of operating temperature.

### Electrical Characteristics Curve

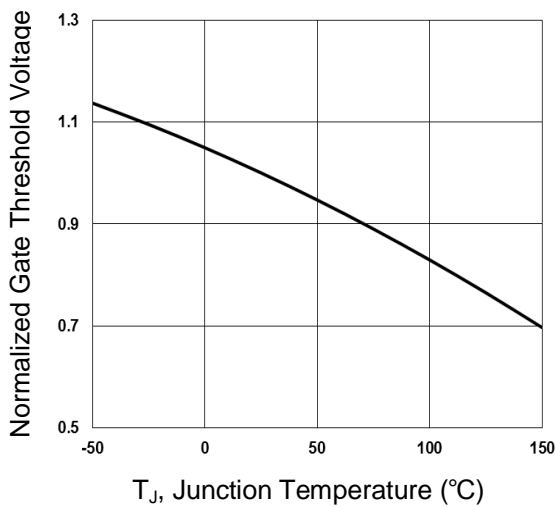
**Continuous Drain Current vs. Tc**



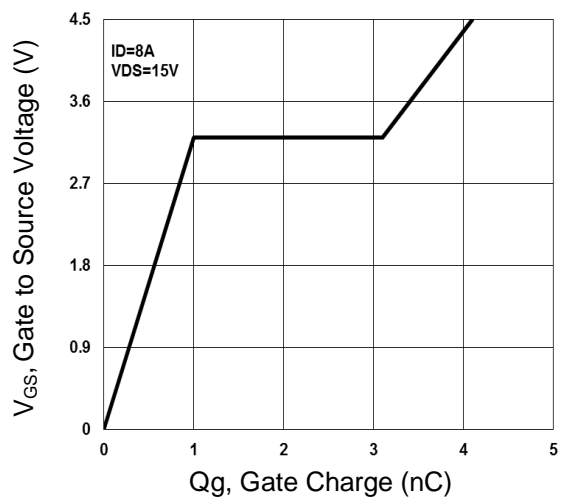
**Normalized R<sub>DS(on)</sub> vs. T<sub>J</sub>**



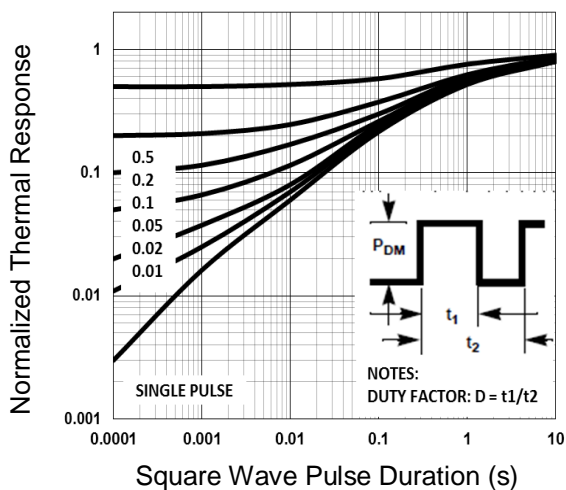
**Normalized V<sub>th</sub> vs. T<sub>J</sub>**



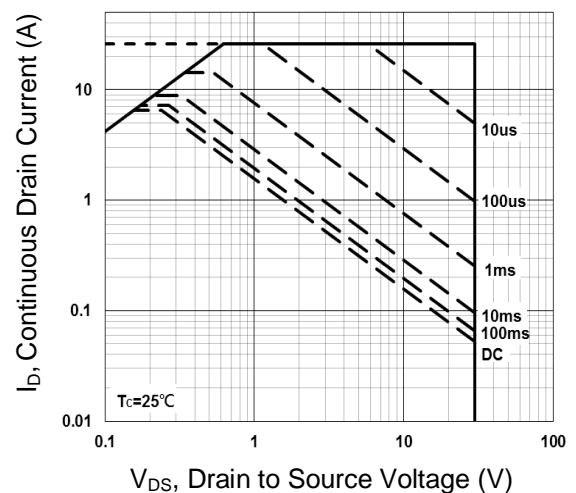
**Gate Charge Waveform**



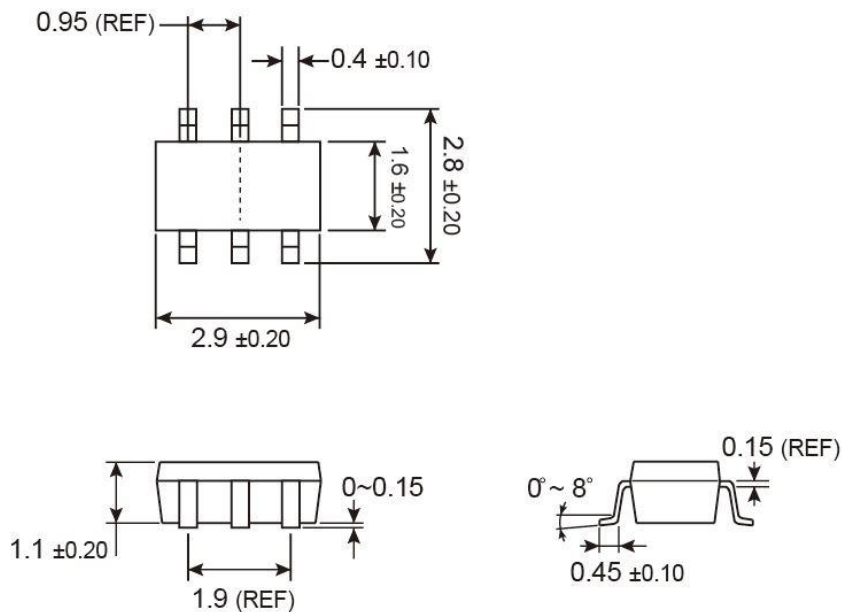
**Normalized Transient Impedance**



**Maximum Safe Operation Area**

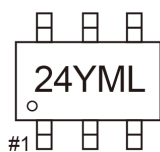


### SOT-26 Mechanical Drawing



Unit: Millimeters

### Marking Diagram



- 24** = Device Code
- Y** = Year Code
- M** = Month Code for Halogen Free Product  
(**O**=Jan, **P**=Feb, **Q**=Mar, **R**=Apr, **S**=May, **T**=Jun, **U**=Jul, **V**=Aug, **W**=Sep, **X**=Oct, **Y**=Nov, **Z**=Dec)
- L** = Lot Code

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